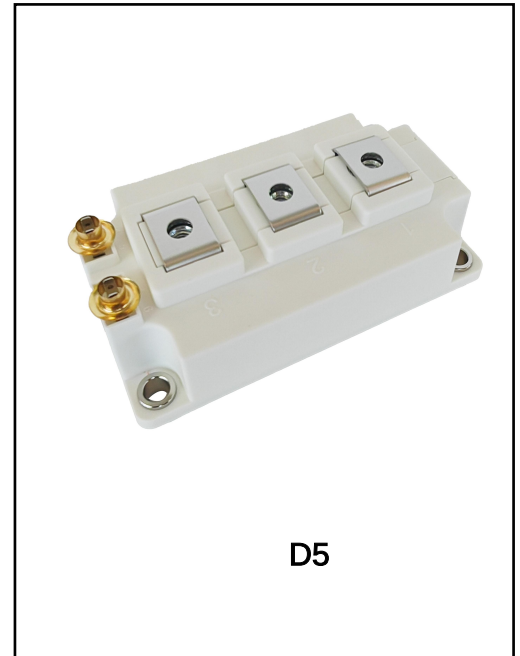


D5 PACK module with AIKO IGBT and Emitter Controlled 7 diode

Features

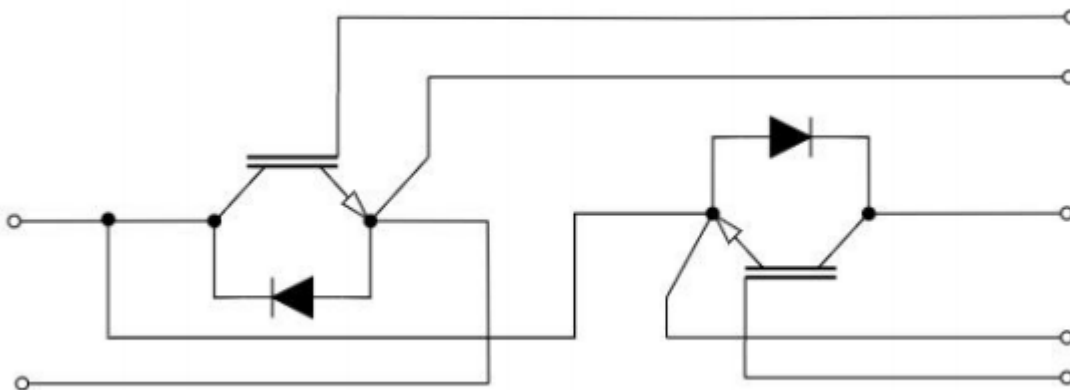
- 1200V Trench Stop IGBTs
- $T_{vj\ op}=150^{\circ}\text{C}$
- V_{CEsat} with positive temperature coefficient
- 10 μs short circuit capability
- Standard housing
- 4 kV AC 1 min insulation
- Low inductance case
- Insulated copper baseplate using DBC technology
- High creepage and clearance distances



Typical Applications

- UPS System
- Photovoltaic
- Motor drive

Description



Package Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, f=50Hz, t=60s	4.0	kV
Internal isolation		basic insulation(class 1, IEC 61140)	Improved Al_2O_3	
Creepage distance	d_{creep}	terminal to heatsink	29.0	mm
Creepage distance	d_{creep}	terminal to terminal	23.0	mm
Clearance	d_{clear}	terminal to heatsink	23.0	mm
Clearance	d_{clear}	terminal to terminal	11.0	mm
Comparative tracking index (electrical)	CTI		>500	
RTI Elec.	RTI	housing	140	°C

Package Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Stray Inductance	L_{CE}			--	20	--	nH
Module Lead Resistance, Terminal to Chip	$R_{CC+EE'}$	$T_c=25^{\circ}C$, per switch		--	0.5	--	mΩ
Storage Temperature Range	T_{STG}			-40		125	°C
M	Mounting torque for module mounting	-Mounting according to valid application note	M5, Screw	3.0	--	6.0	Nm
M	Terminal connection torque	-Mounting according to valid application note	M6, Screw	2.5	--	5.0	Nm
Weight	G			--	340	--	g

IGBT

Absolute Maximum Ratings (T_C = 25°C unless otherwise noted)

Symbol	Description	Note or test condition		Value	Unit
V _{CES}	Collector-Emitter Voltage	T _{vj} = 25 °C		1200	V
I _{CDC}	Continuous DC collector current	T _{vj max} = 175 °C	T _C = 90 °C	200	A
I _{CRM}	Repetitive peak collector current	t _p limited by T _{vj op}		400	A
V _{GES}	Gate-emitter peak voltage			±30	V

Characteristics (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition		Min	Typ	Max	Unit
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 200A, V _{GE} = 15 V	T _{vj} = 25 °C	--	1.45	1.95	V
			T _{vj} = 150 °C	--	1.70	--	
			T _{vj} = 175 °C	--	1.75	--	
V _{GE(TH)}	Gate-Emitter Threshold Voltage	V _{GE} = V _{CE} , I _C = 5 mA, T _{vj} = 25°C		5.0	5.8	6.5	V
I _{CES}	Collector-Emitter Cutoff Current	V _{GE} = 0 V, V _{CE} = 1200V, T _{vj} = 25°C		--	--	100	uA
I _{GES}	Gate-Emitter Leakage Current	V _{GE} = ±30 V, V _{CE} = 0 V, T _{vj} = 25°C		--	--	±100	nA
R _{Gint}	Internal Gate Resistance	T _{vj} = 25 °C		--	1.34	--	Ω
C _{ies}	Input Capacitance	f = 100 kHz, T _{vj} = 25 °C, V _{CE} = 25 V, V _{GE} = 0 V		--	34	--	nF
C _{oes}	Out Capacitance			--	0.8	--	nF
C _{res}	Reverse Transfer Capacitance			--	0.12	--	nF
Q _G	Gate Charge	V _{GE} = ±15 V, V _{CC} = 960 V		--	1.10	--	μC
t _{d(on)}	Turn-On Delay Time	I _C = 200A, V _{CC} = 600 V, V _{GE} = 15 /-5V, R _G = 1.0 Ω	T _{vj} = 25 °C	--	0.203	--	μS
			T _{vj} = 150 °C	--	0.230	--	
			T _{vj} = 175 °C	--	0.233	--	
t _r	Rise Time	I _C = 200A, V _{CC} = 600 V, V _{GE} = 15 /-5V, R _G = 1.0 Ω	T _{vj} = 25 °C	--	0.037	--	μS
			T _{vj} = 150 °C	--	0.044	--	
			T _{vj} = 175 °C	--	0.045	--	
t _{d(off)}	Turn-off Delay Time	I _C = 200A, V _{CC} = 600 V, V _{GE} = 15 /-5V, R _{Goff} = 1.0 Ω	T _{vj} = 25 °C	--	0.412	--	μS
			T _{vj} = 150 °C	--	0.470	--	
			T _{vj} = 175 °C	--	0.480	--	
t _f	Fall Time	I _C = 200A, V _{CC} = 600 V, V _{GE} = 15 /-5V, R _G = 1.0 Ω	T _{vj} = 25 °C	--	0.050	--	μS
			T _{vj} = 150 °C	--	0.112	--	
			T _{vj} = 175 °C	--	0.114	--	
E _{on}	Turn-On Switching Loss per Pulse	I _C = 200A, V _{CC} = 600 V, V _{GE} = 15 /-5V, R _G = 1.0 Ω (T _{vj max} = 175 °C)	T _{vj} = 25 °C	--	6.22	--	mJ
			T _{vj} = 150 °C	--	12.40	--	
			T _{vj} = 175 °C	--	13.80	--	
E _{off}	Turn Off Switching Loss per Pulse	I _C = 200A, V _{CC} = 600 V, V _{GE} = 15 /-5V, R _G = 1.0 Ω (T _{vj max} = 175 °C)	T _{vj} = 25 °C	--	27.03	--	mJ
			T _{vj} = 150 °C	--	36.00	--	
			T _{vj} = 175 °C	--	37.20	--	

I _{SC}	SC Data	V _{GE} ≤ 15 V, V _{CC} = 800 V, V _{CEmax} =V _{CES} -L _{SCE} .di/dt	t _p ≤ 10 μs, T _{vj} =150 °C	--	1000	--	A
			t _p ≤ 10 μs, T _{vj} =175 °C	--	941	--	
R _{thJC}	Thermal resistance	Junction-to-Case (per IGBT)		--	0.157	--	K/W
T _{vj op}	Temperature under switching conditions			-40		175 ¹⁾	°C

¹⁾T_{vj op} > 175 °C is only allowed for operation at overload conditions.

Diode

Absolute Maximum Ratings (T_C = 25 °C unless otherwise noted)

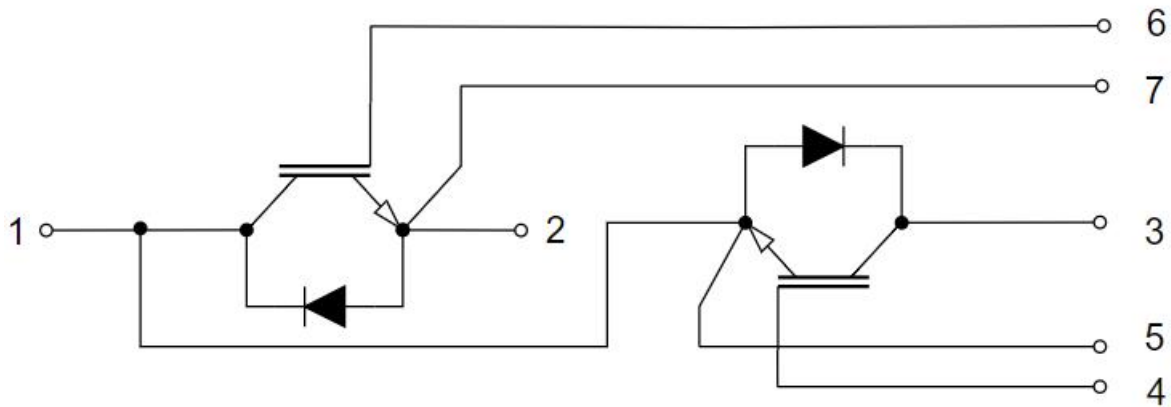
Symbol	Description	Note or test condition	Value	Unit
V _{RRM}	Repetitive peak reverse voltage	T _{vj} = 25 °C	1200	V
I _F	Continuous DC forward current		200	A
I _{FRM}	Repetitive peak forward current	t _p = 1 ms	400	A

Characteristics (T_C=25 °C unless otherwise noted)

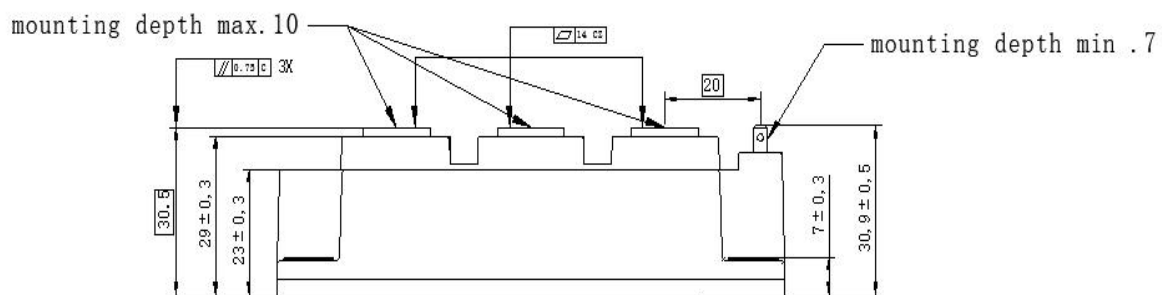
Characteristics (T _C =25 °C unless otherwise noted)							
Symbol	Parameter	Test Condition		Value			Unit
				Min	Typ	Max	
V _F	Diode Forward Voltage	I _F = 200A, V _{GE} = 0 V	T _{vj} = 25 °C	--	2.10	2.80	V
			T _{vj} = 150 °C	--	2.00	--	
			T _{vj} = 175 °C	--	1.95	--	
Q _{rr}	Recovered Charge	I _C = 200A, V _{CC} = 600 V, V _{GE} = 15 /-5V, R _G = 1.0 Ω (T _{vj max} = 175 °C)	T _{vj} = 25 °C	--	4.1	--	μC
			T _{vj} = 150 °C	--	13.5	--	
			T _{vj} = 175 °C	--	16.5	--	
I _{RRM}	Peak Reverse Recovery Current	I _C = 200A, V _{CC} = 600 V, V _{GE} = 15 /-5V, R _G = 1.0 Ω (T _{vj max} = 175 °C)	T _{vj} = 25 °C	--	140	--	A
			T _{vj} = 150 °C	--	176	--	
			T _{vj} = 175 °C	--	185	--	
E _{rec}	Reverse recovery energy	I _C = 200A, V _{CC} = 600 V, V _{GE} = 15 /-5V, R _G = 1.0 Ω (T _{vj max} = 175 °C)	T _{vj} = 25 °C	--	4.4	--	mJ
			T _{vj} = 150 °C	--	12.0	--	
			T _{vj} = 175 °C	--	14	--	
R _{thJC}	Thermal resistance, junction to case	per diode		--	0.154	--	K/W
T _{vj op}	Temperature under switching conditions			-40	--	175 ²⁾	°C

²⁾T_{vj op} > 175 °C is only allowed for operation at overload conditions.

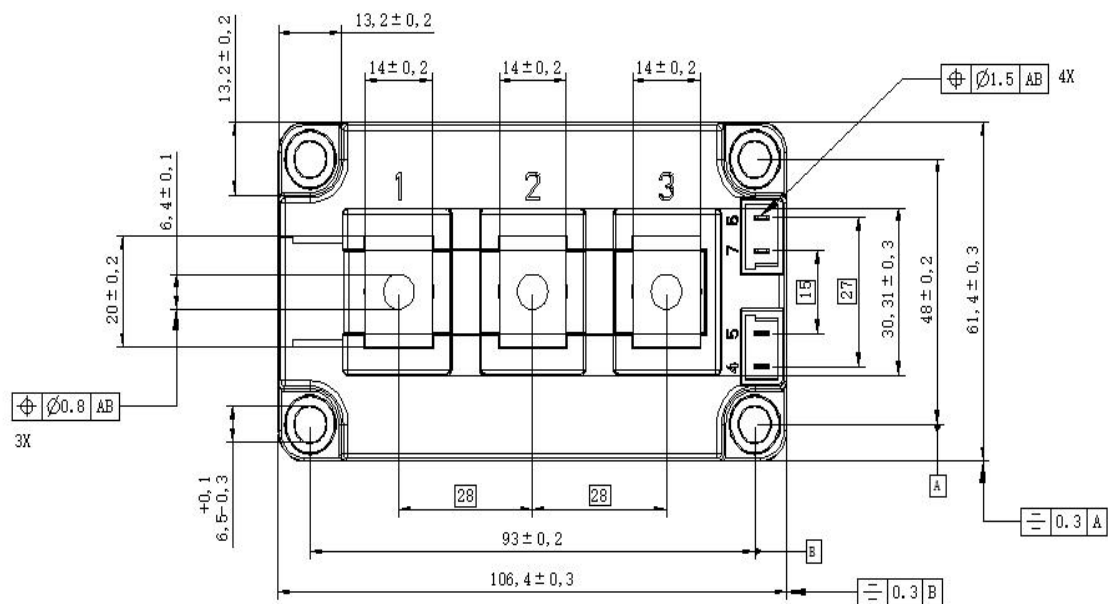
CIRCUIT DIAGRAM



PACKAGE DIMENSION



SIDE VIEW



TOP VIEW